

# MX1516C LDMOS TRANSISTOR

Document Number: MX1516C  
Product Datasheet V1.2

## 60W, 12.5V High Power RF LDMOS FETs

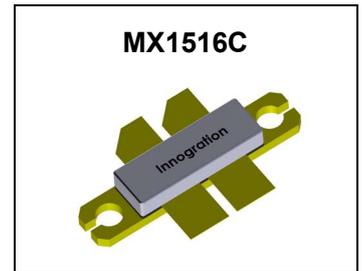
### Description

The MX1516C is a 60-watt capable, highly rugged, unmatched, push pull LDMOS FET, designed for wide-band commercial and industrial applications with frequencies HF to 600MHz.

- Typical Performance (On Innogration fixture with device soldered):

$V_{DD} = 12$  Volts,  $I_{DQ} = 800$  mA, CW.

Freq(MHz)	Pin(dBm)	P3dB(dBm)	P3dB(W)	IDS(A)	Gain(dB)	Eff(%)
2	23.3	48.2	66	7.6	24.9	69.47%
5	22.6	48.2	66	7.5	25.6	70.40%
10	22.6	48.2	66	7.49	25.6	70.49%
15	23.5	48.15	65	7.55	24.65	68.87%
20	24.2	48.1	64	7.53	23.9	67.99%
25	24.5	48.1	64	7.7	23.6	66.49%
30	23.6	47.9	61	7.6	24.3	64.21%
35	25.2	47.8	60	7.73	22.6	62.10%
40	26.4	47.5	56	7.38	21.1	60.70%
45	27.4	47.7	58	7.86	20.3	59.03%
50	27.2	47.9	61	8.2	20.7	59.51%
54	28.2	48	63	8.39	19.8	60.07%



### Features

- High Efficiency and Linear Gain Operations
- Integrated ESD Protection
- Excellent thermal stability, low HCI drift
- Large Positive and Negative Gate/Source Voltage Range for Improved Class C Operation
- Pb-free, RoHS-compliant

### Suitable Applications

- 2-30MHz (HF or Short wave communication)
- 30-88MHz (Ground communication)
- 54-88MHz (TV VHF I)
- 88-108MHz (FM)
- 118 -140MHz (Avionics)
- 136-174MHz (Commercial ground communication)
- 160-230MHz (TV VHF III)
- 30-512MHz (Jammer, Ground/Air communication)
- 100kHz - 100MHz (ISM, instrumentation)

**Table 1. Maximum Ratings**

Rating	Symbol	Value	Unit
Drain--Source Voltage	$V_{DSS}$	+65	Vdc
Gate--Source Voltage	$V_{GS}$	-10 to +10	Vdc

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Operating Voltage	$V_{DD}$	+32	Vdc
Storage Temperature Range	$T_{stg}$	-65 to +150	°C
Case Operating Temperature	$T_c$	+150	°C
Operating Junction Temperature	$T_j$	+225	°C

**Table 2. Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case $T_c = 85^\circ\text{C}$ , $P_{out} = 60\text{W}$ , CW Test	$R_{\theta JC}$	0.38	°C/W

**Table 3. ESD Protection Characteristics**

Test Methodology	Class
Human Body Model (per JESD22--A114)	Class 2

**Table 4. Electrical Characteristics** ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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**DC Characteristics (per half section)**

Drain-Source Voltage $V_{GS} = 0$ , $I_{DS} = 1.0\text{mA}$	$V_{(BR)DSS}$	65			V
Zero Gate Voltage Drain Leakage Current ( $V_{DS} = 75\text{V}$ , $V_{GS} = 0\text{V}$ )	$I_{DSS}$	—	—	1	$\mu\text{A}$
Zero Gate Voltage Drain Leakage Current ( $V_{DS} = 28\text{V}$ , $V_{GS} = 0\text{V}$ )	$I_{DSS}$	—	—	1	$\mu\text{A}$
Gate--Source Leakage Current ( $V_{GS} = 10\text{V}$ , $V_{DS} = 0\text{V}$ )	$I_{GSS}$	—	—	1	$\mu\text{A}$
Gate Threshold Voltage ( $V_{DS} = 12.5\text{V}$ , $I_D = 400\ \mu\text{A}$ )	$V_{GS(th)}$	—	2	—	V
Gate Quiescent Voltage ( $V_{DD} = 12.5\text{V}$ , $I_D = 200\text{mA}$ , Measured in Functional Test)	$V_{GS(Q)}$	—	2.48	—	V

**Functional Tests** (In Demo Test Fixture, 50 ohm system)  $V_{DD} = 12.5\text{Vdc}$ ,  $I_{DQ} = 200\text{mA}$ ,  $f = 30\text{MHz}$ , CW Signal Measurements,  $P_{in} = 23.6\text{dBm}$

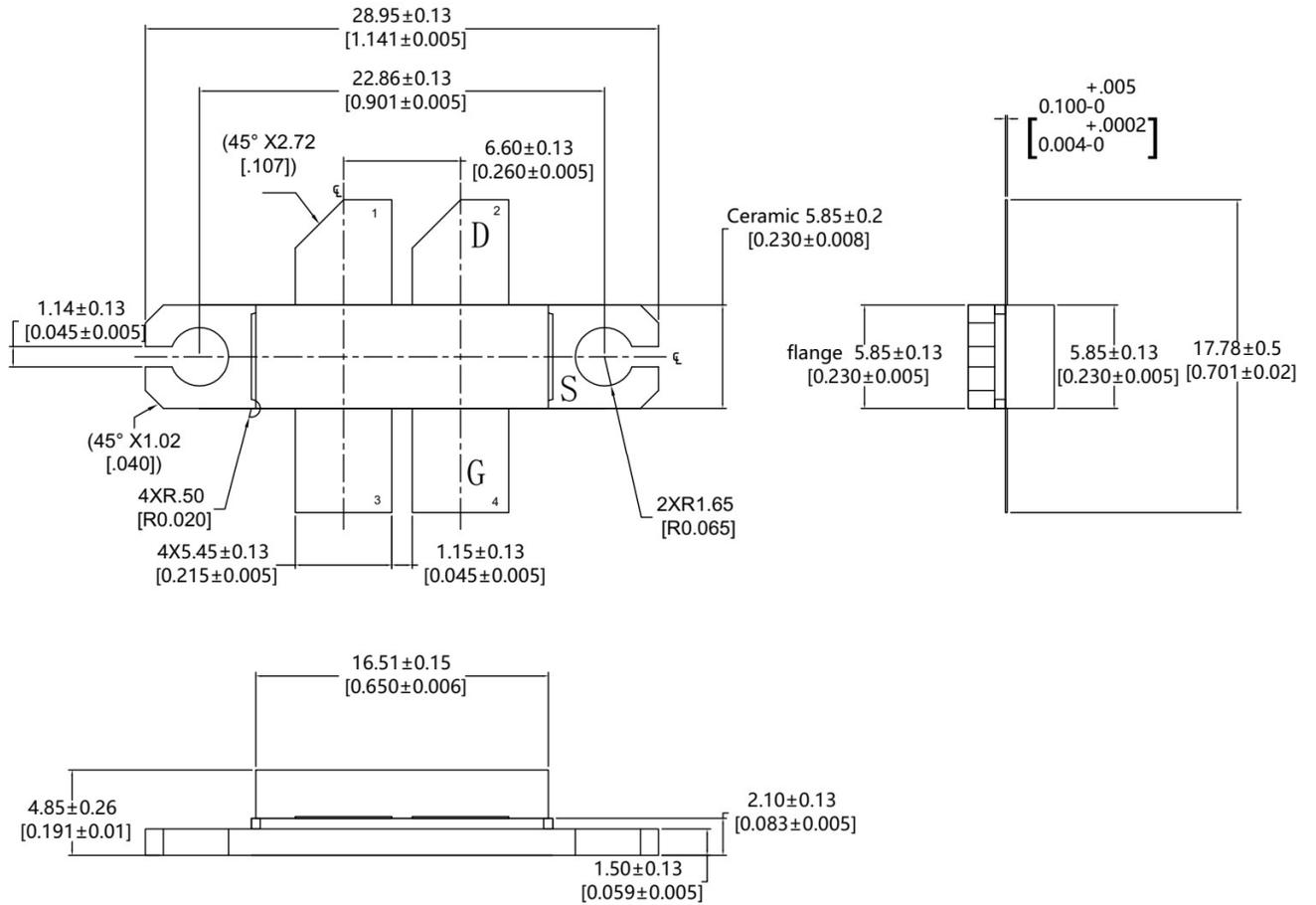
Power Gain	$G_p$	—	18	—	dB
Drain Efficiency@Pout	$\eta_D$	—	64	—	%
Output Power	$P_{out}$	—	60	—	W
Input Return Loss	IRL	—	-7	—	dB

**Load Mismatch (In Innogration Test Fixture, 50 ohm system):**  $V_{DD} = 12.5\text{Vdc}$ ,  $I_{DQ} = 200\text{mA}$ ,  $f = 2\text{MHz}$

Load open and short, at 60W CW	No Device Degradation
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## Package Outline

Flanged ceramic package; 2 mounting holes; 4 leads



OUTLINE VERSION	REFERENCE			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
PKG-LB/LBB					05/21/2021

## Revision history

Table 5. Document revision history

Date	Revision	Datasheet Status
2018/9/29	Rev 1.0	Product Datasheet Creation
2020/3/9	Rev 1.1	Modify typo on 1 <sup>st</sup> page
2022/9/19	Rev 1.2	LBB Outline updated

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